

Design of High-Power Free-Electron Lasers for EUV Lithography Applications

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ERL-EUV Feasibility Study Group



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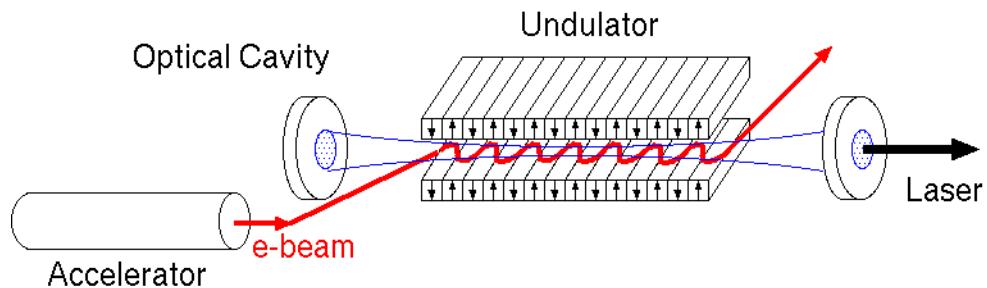
(JAEA) R. Hajima, N. Nishimori

The feasibility study has been done under collaboration with a Japanese company.

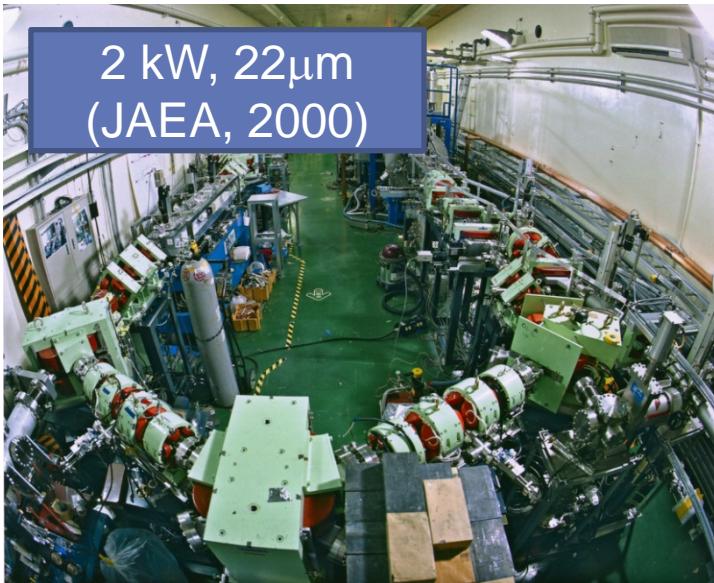
See also

E. Kako (KEK); “Development of Superconducting Accelerator with ERL for EUV-FEL” in this Workshop

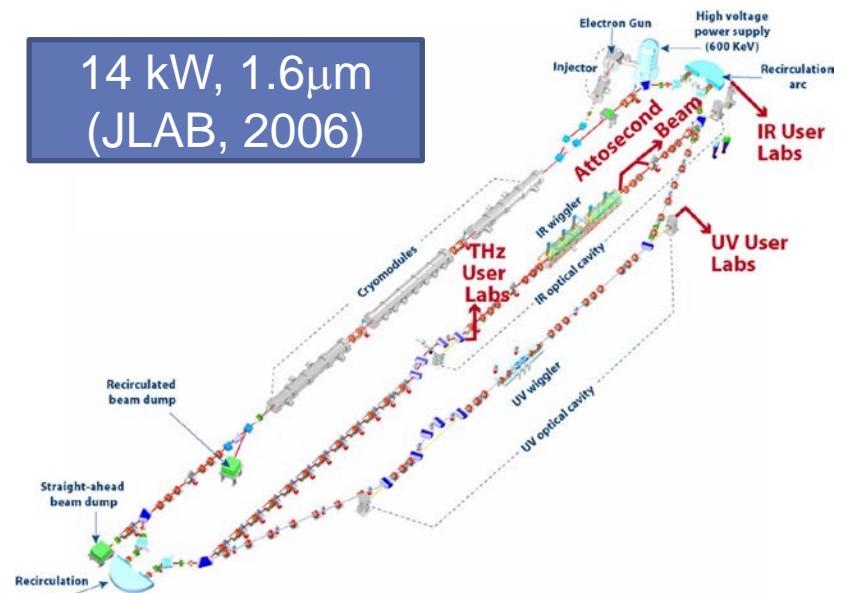
High-Power FELs



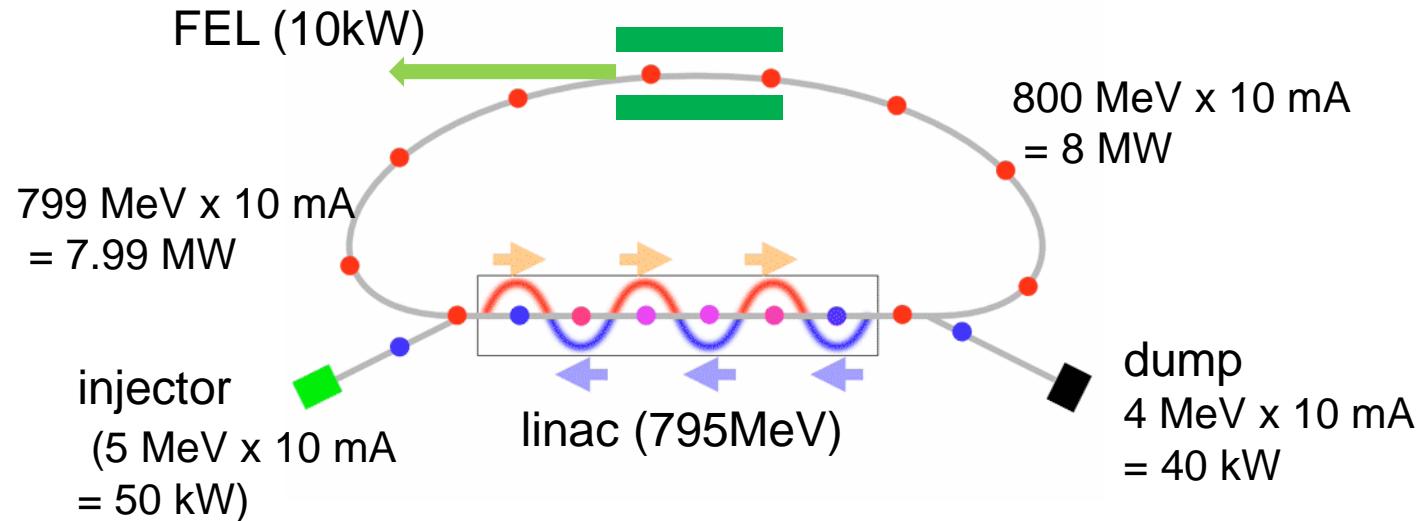
Laser Medium = Vacuum
→ free from the thermal limit



14 kW, 1.6μm
(JLAB, 2006)



Energy Recovery Linac is a Key



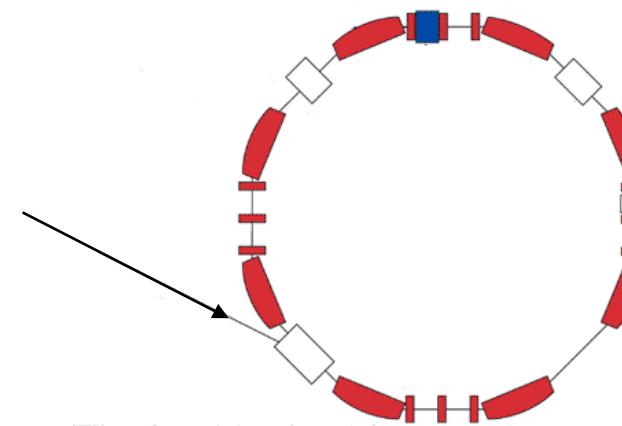
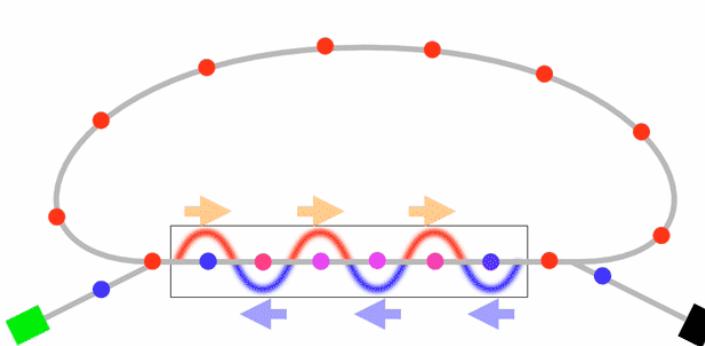
Energy Recovery Linac = ERL

can save wall-plug power

can reduce dump energy = small radiation



ERLs are not Storage Rings



- ✓ Fresh electrons always
- ✓ Recycle energy at the linac
- ✓ Emittance is dominated by injector
- ✓ Flexible e-bunch compression



Allow e-beams tailored to FEL
> 10kW for IR

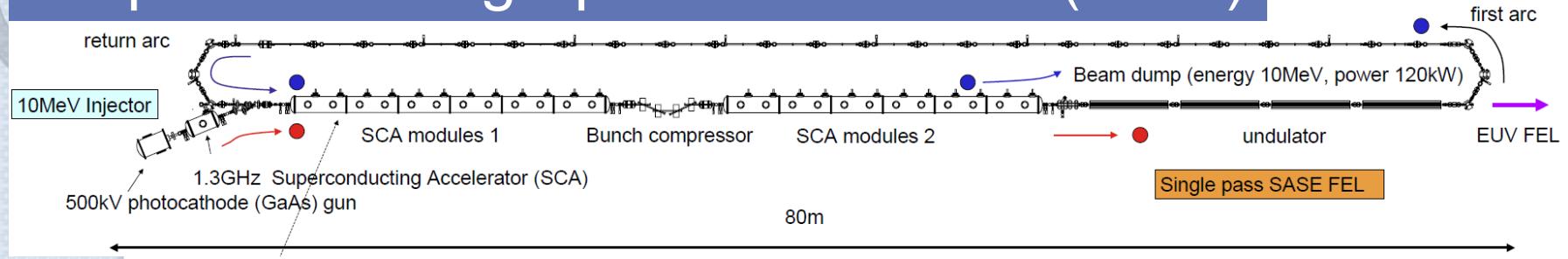
- ✓ Re-use electrons many times
- ✓ Compensate energy loss by RF
- ✓ Bunch length and emittance are dominated by ring design



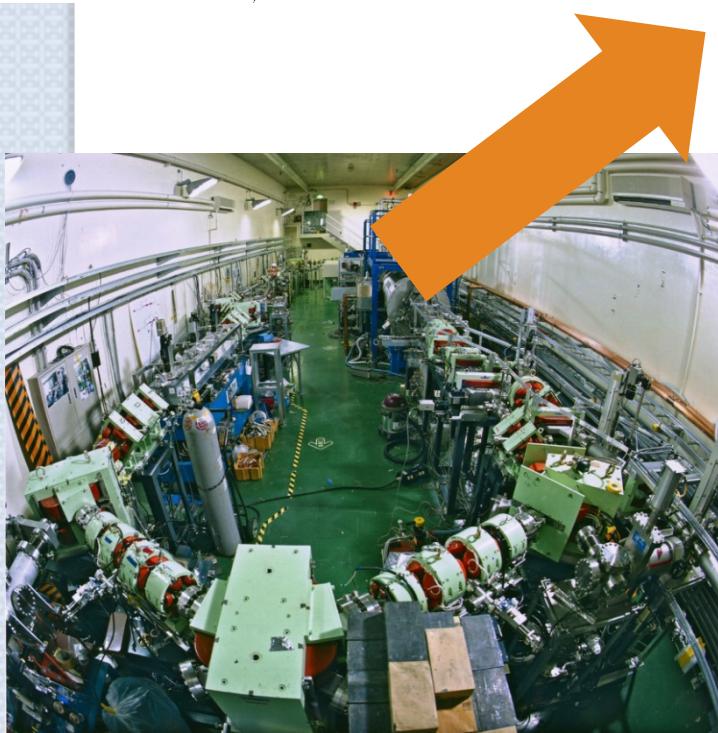
FEL is limited by e-beam heating
<1 W for VUV

From IR to EUV

Proposal of a high-power EUV FEL (2006)



R. Hajima et al., EUV Source WS (2006)



$$\lambda = \lambda_u \frac{1 + a_w^2}{2\gamma^2}$$

$$\gamma = \frac{E}{mc^2}$$

FEL is scalable from IR to EUV

However, several challenges exist to shorten FEL wavelength.

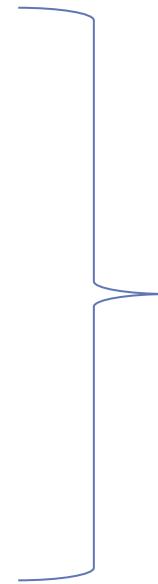
FEL Physics – a minimum set

FEL gain parameter

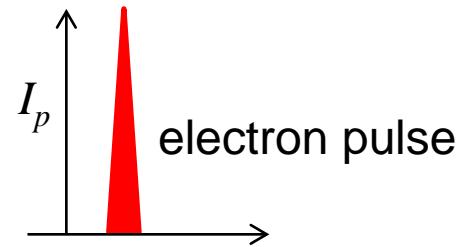
$$\rho = \left[\frac{1}{16} \frac{I_p K_u^2 [JJ]^2}{I_A \gamma^3 \sigma_x^2 k_u^2} \right]^{1/3}$$

gain length

$$L_G = \frac{\lambda_u}{4\pi\sqrt{3}\rho}$$



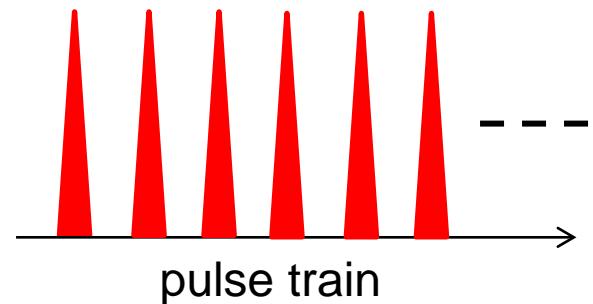
- shorter wavelength
→ higher energy of electron
→ higher peak current



FEL power

$$P_{FEL} \approx \rho P_{electron}$$

$$P_{electron} = E \times I_{ave}$$

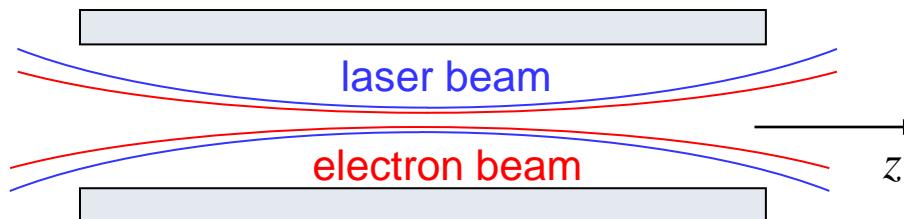


E-beam Emittance

e-beam envelope < laser beam

$$\sigma(z) = \sigma_0 \sqrt{1 + (z/\beta_0)^2}$$
$$\sigma^2 = \epsilon \beta_0$$

$$w(z) = w_0 \sqrt{1 + (z/Z_R)^2}$$
$$w_0^2 = \lambda Z_R / \pi$$

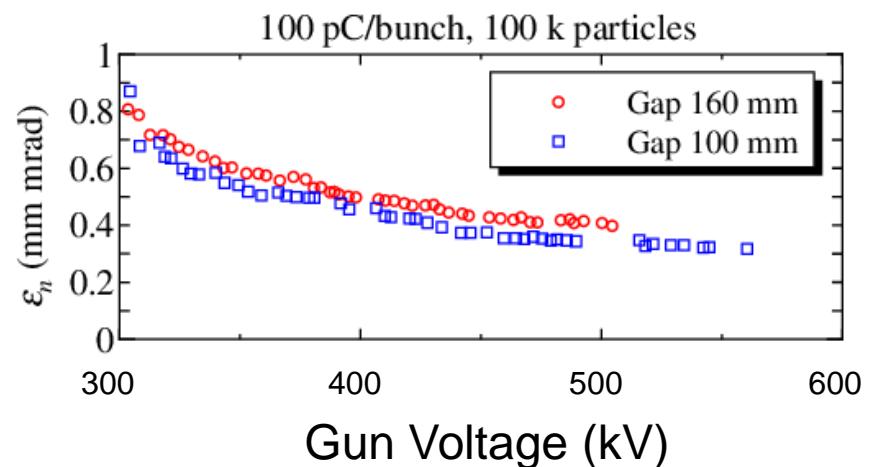
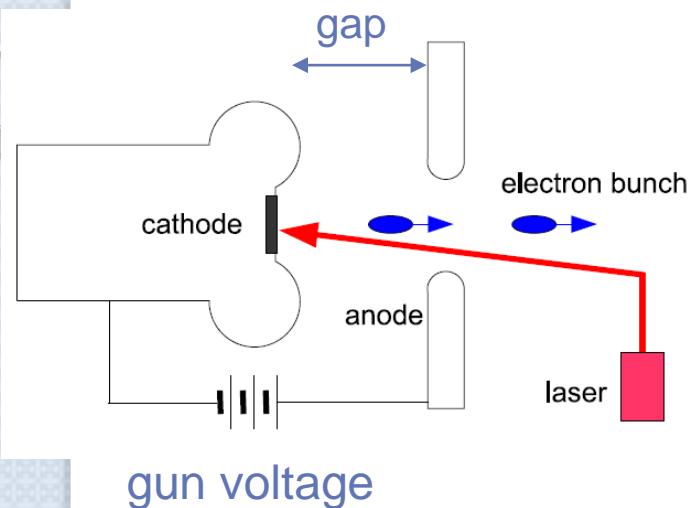


For efficient FEL interaction, an electron beam must have small emittance:

$$\epsilon \leq \frac{\lambda}{4\pi} \quad \text{or} \quad \frac{\epsilon_n}{\gamma} \leq \frac{\lambda}{4\pi}$$

Normalized emittance $\epsilon_n \equiv \gamma \epsilon$

Gun Voltage vs Emittance

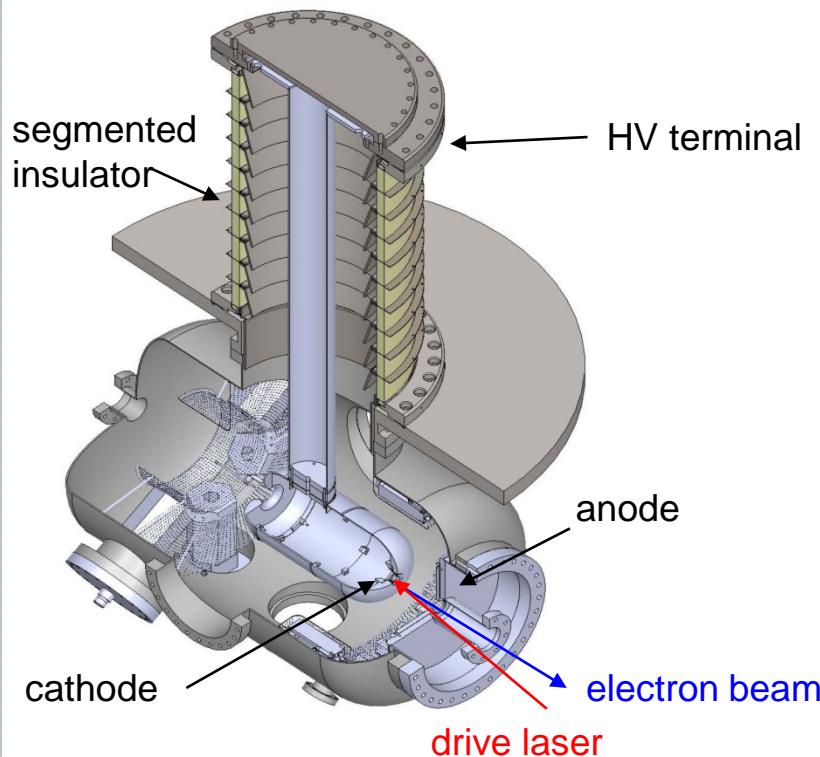
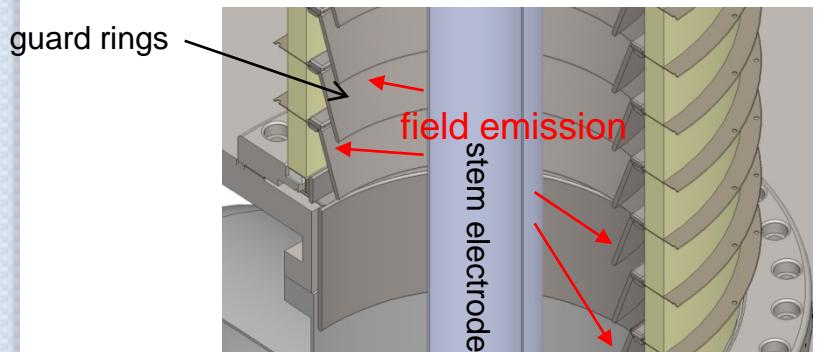


T. Miyajima et al., Proc. FEL Conf. 2014.

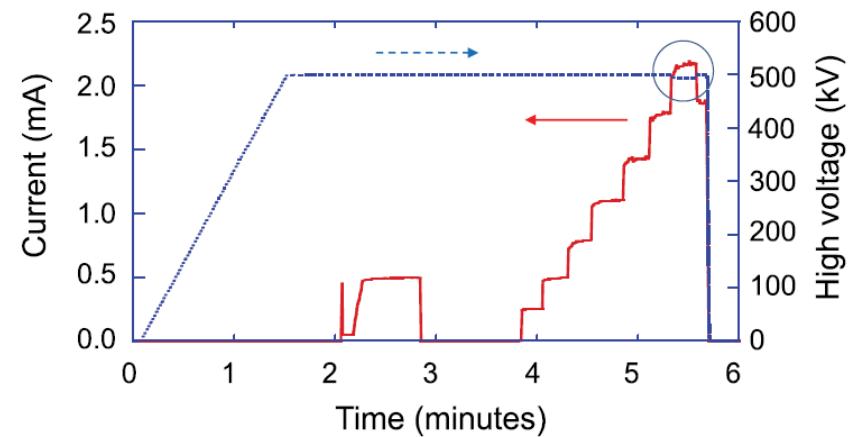
electron bunch of high density
→ space charge repulsion
→ emittance growth

Gun voltage must be high enough!

Development of a 500-kV DC gun



limited <350kV by damage of ceramic due to field emission
↓
solved by segmented insulator and guard rings
↓
generation of 500-keV beams!



N. Nishimori et al., App. Phys. Lett. (2013)

Many Trade Offs in FEL design

| | small | | large |
|---------------|------------------------------------|--|------------------------------------|
| E-beam energy | small foot print small FEL gain | | large foot print large FEL gain |
| Rep. rate | more HOM's | | less HOM's |
| Bunch charge | small emittance small current | | large emittance large current |
| Acc. gradient | long linac small cryoplant | | short linac large cryoplant |
| Undulator gap | small pitch more heat load | | long pitch less heat load |
| | | | |

- ✓ Consider technology readiness
- ✓ Choose parameters with analytical formulae
- ✓ Confirm parameters with numerical simulations

Examples of Parameter Set

| | JAEA (2006) | JAEA/KEK (2014)-A | JAEA/KEK (2014)-B |
|-----------------------------------|----------------|-------------------|-------------------|
| FEL ^(#) | 13 nm, 14 kW | 13 nm, 12 kW | 13 nm, 13 kW |
| e-beam | | | |
| energy, ave. current | 580 MeV, 12 mA | 800 MeV, 8 mA | 1200 MeV, 8 mA |
| bunch charge | 325 pC | 100 pC | → |
| norm. emittance | 0.8 mm-mrad | 0.8 mm-mrad | 0.9 mm-mrad |
| peak current | 1300 A | 1000 A | 670 A |
| rep. rate | 36 MHz | 81.25 MHz | 81.25 MHz |
| undulator | | | |
| gap | 6 mm | 7 mm | 20 mm |
| pitch | 20 mm | 26 mm | 48 mm |
| K | 1.17 | 1.69 | 1.98 |
| saturation length ^(##) | 40 m | 55 m | 90 m |

(#) including undulator tapering

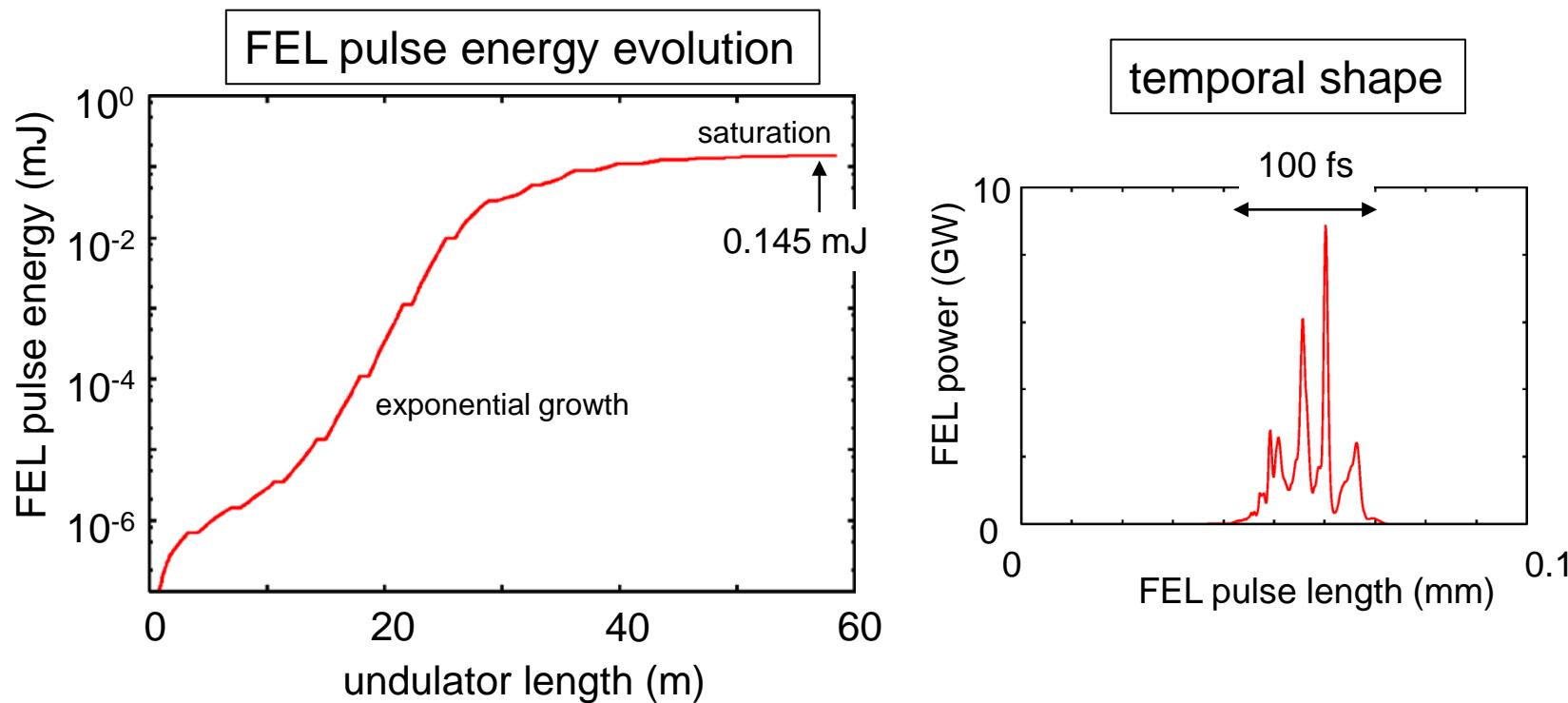
(##) including undulator intervals for quadrupole focusing

Simulation: FEL pulse evolution

GENESIS simulations by N. Nishimori

JAEA/KEK (2014)-A:

$E=800 \text{ MeV}$, $q=100 \text{ pC}$, $I_p=1000 \text{ A}$, $\varepsilon_n=0.8 \text{ mm-mrad}$,
rep.=81.25 MHz

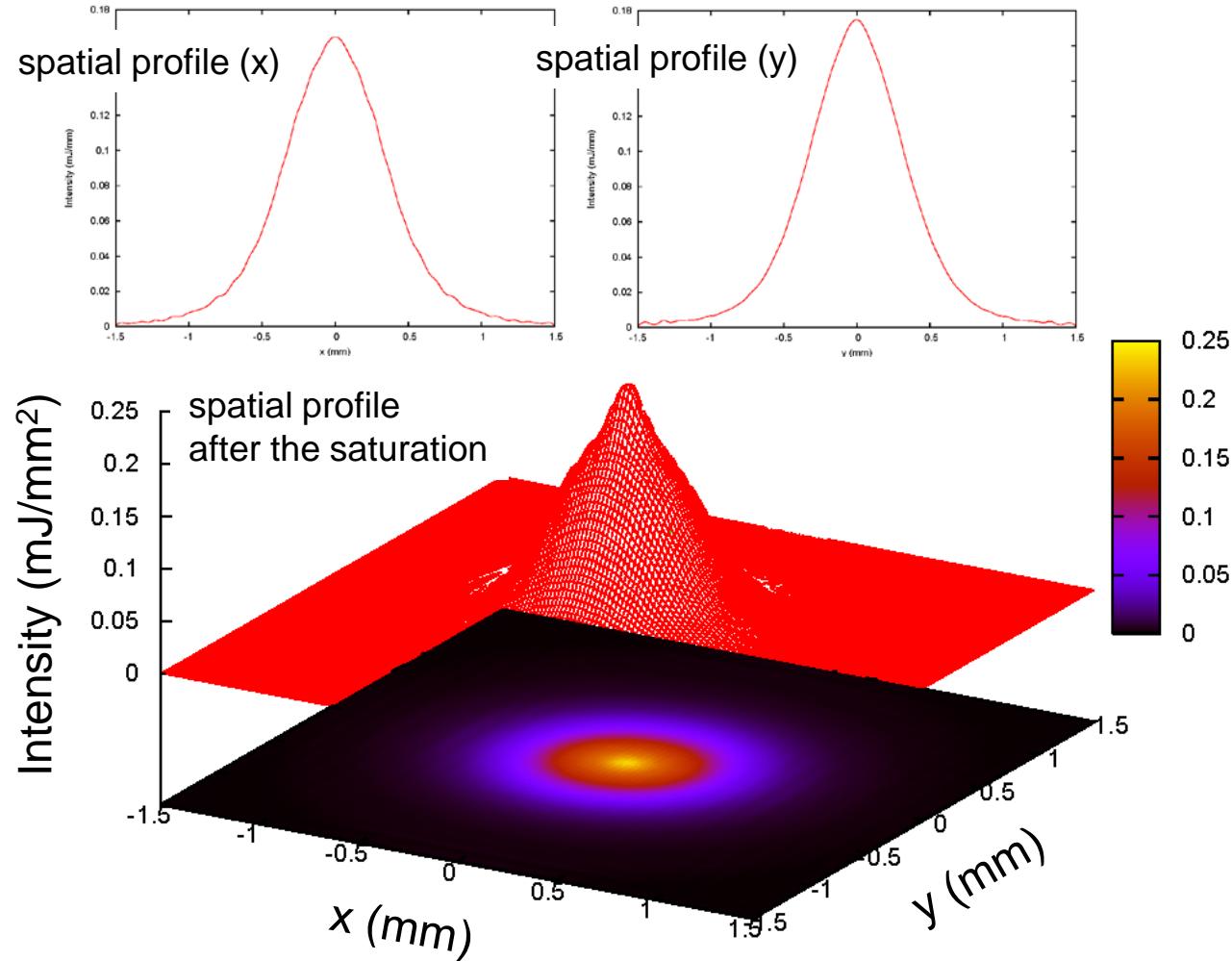


$$0.145 \text{ mJ} \times 81.25 \text{ MHz} = 12 \text{ kW}$$

Simulation: spatial pattern

JAEA/KEK (2014)-A:

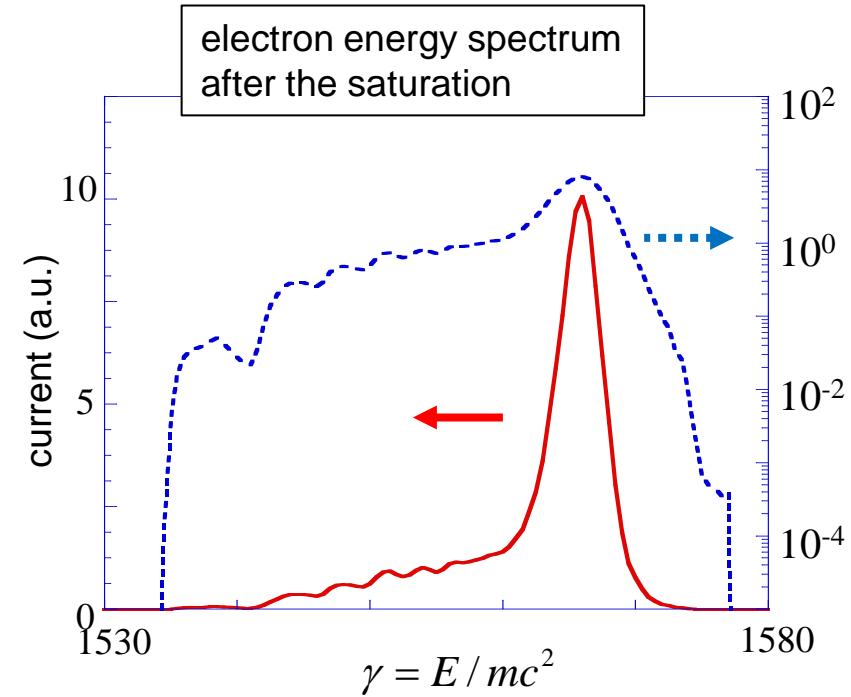
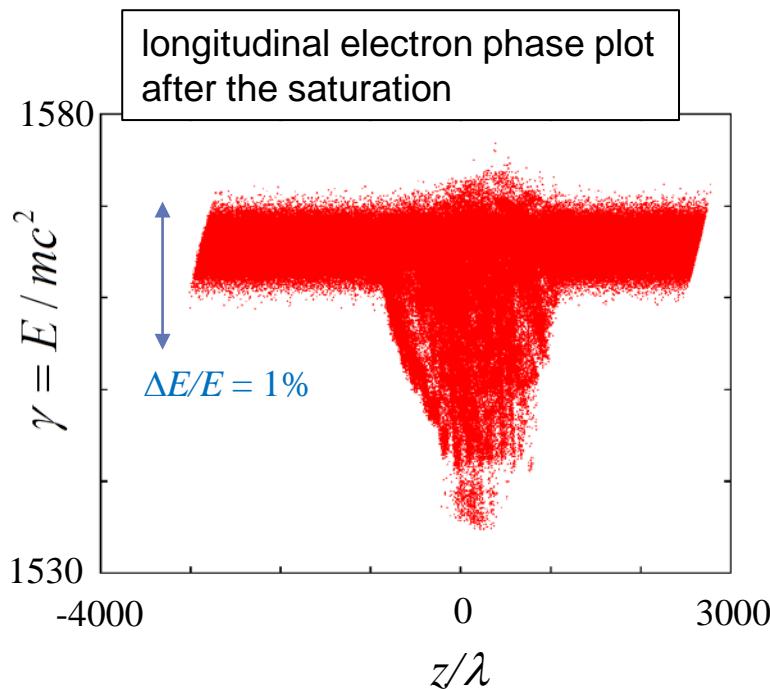
$E=800 \text{ MeV}$, $q=100 \text{ pC}$, $I_p=1000 \text{ A}$, $\varepsilon_n=0.8 \text{ mm-mrad}$,
rep.=81.25 MHz



Simulation: electron energy spread

JAEA/KEK (2014)-A:

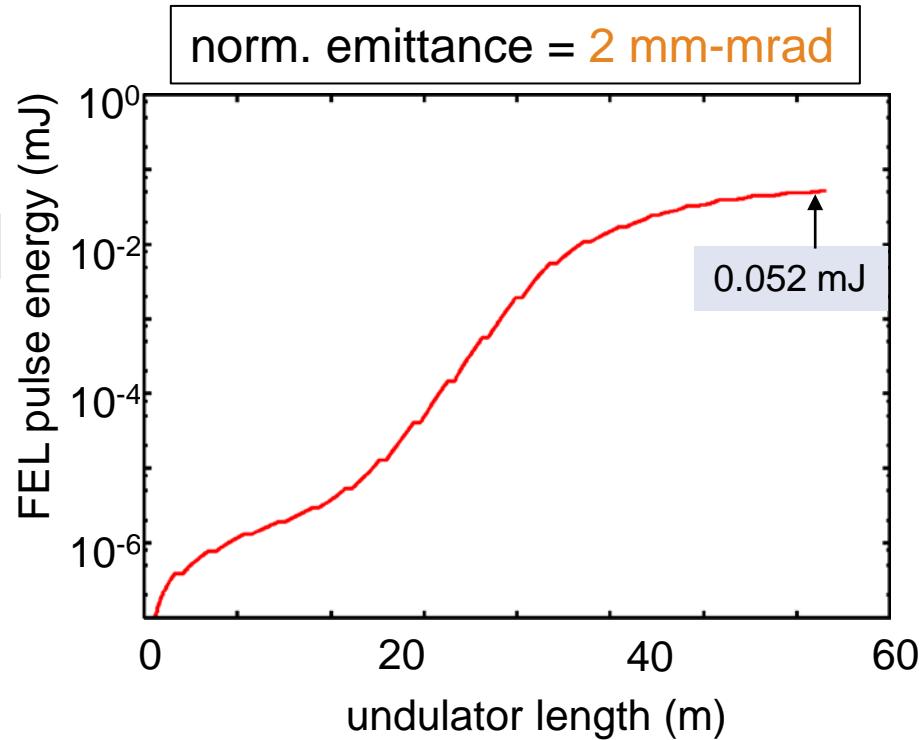
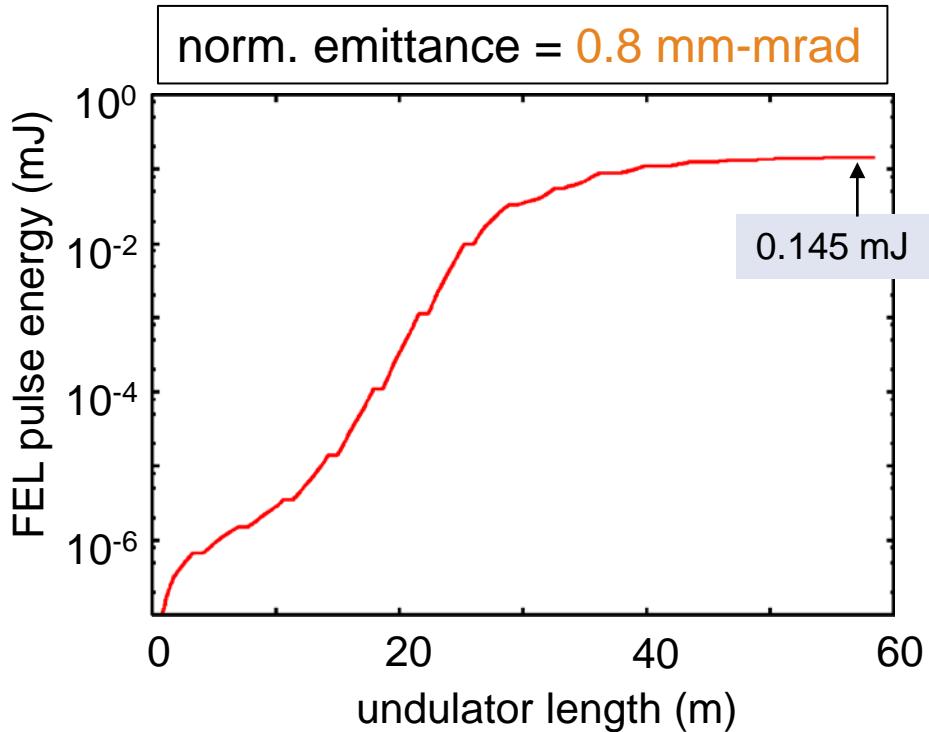
$E=800 \text{ MeV}$, $q=100 \text{ pC}$, $I_p=1000 \text{ A}$, $\varepsilon_n=0.8 \text{ mm-mrad}$,
rep.=81.25 MHz



electron energy spread : 0.1%(rms) \rightarrow 2.6% (full width)
conversion efficiency : 0.18% (from electron to laser)

energy spread of 2.6% is manageable in ERLs

Simulation: emittance and power



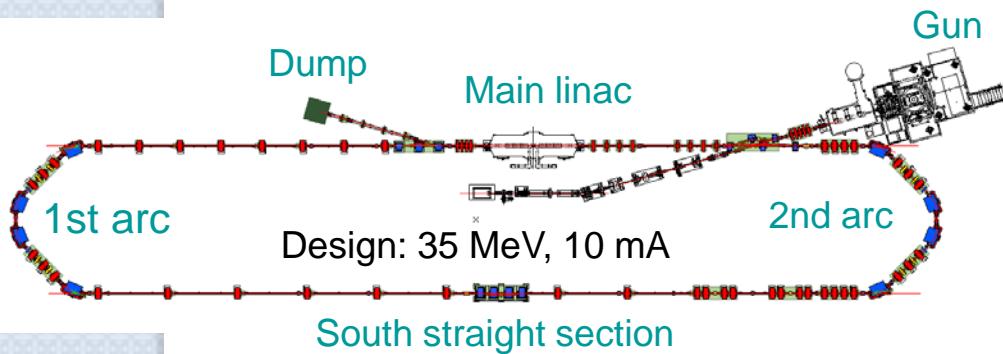
$$0.145 \text{ mJ} \times 81.25 \text{ MHz} = 12 \text{ kW}$$

$$0.052 \text{ mJ} \times 81.25 \text{ MHz} = 4.2 \text{ kW}$$

Small emittance is essential for FEL

Compact ERL – a test facility in operation at KEK

Technology Demo. for future ERL-based light sources
– X-ray, γ -ray and EUV



R&D items

- performance and reliability of components
- small emittance beam
- bunch compression to “fs”

→ Demo. of EUV-quality beam



main linac



South straight section



2nd arc

Beam was successfully accelerated up to 20 MeV in the main linac, decelerated, and transported to the entrance of dump line (Dec. 16-20, 2013)

Beam energy (E)

- Injector: 3.4 MeV
- Recirculation loop: 19.9 MeV

Parameters

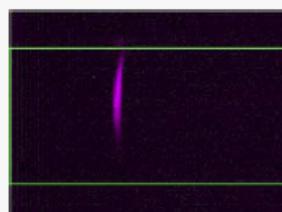
- Gun voltage: 390 kV Buncher: OFF
- Injector cavities: $E_{acc} = (3.6, 3.6, 3.4)$ MV/m
- Main-Linac cavities: $V_c = (8.3, 8.3)$ MV

Beam pulses (macropulse beams)

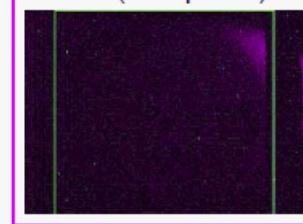
- peak current: ~20 μ A
- macropulse width: 1.2 μ s
- repetition of bunches: 1.3 GHz
- repetition frequency: 3 Hz
- average beam current: ~ 70 pA

Beam profiles observed with screen monitors

MS14

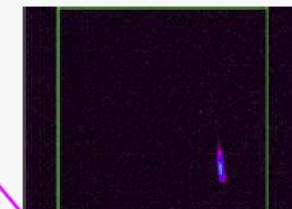


MS31 (dump line)

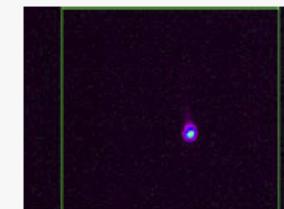


At this time, we could not transport beams to the dump.

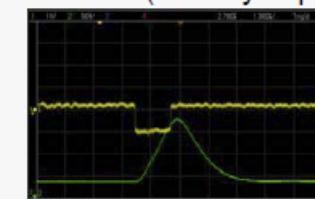
MS11



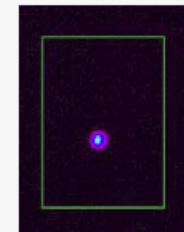
MS3



Gun FC (faraday cup)



MS1

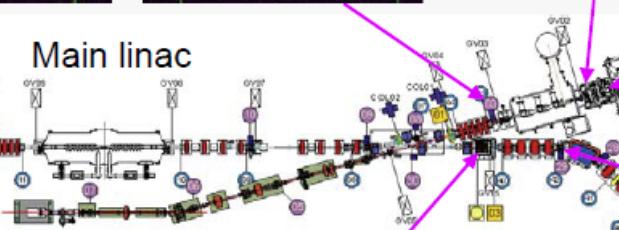


The 1st arc

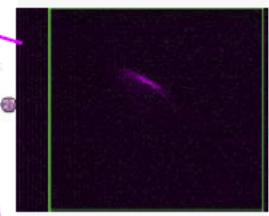


Legend:
● BPM ■ CT
● Screen ■ DCCT

Main linac

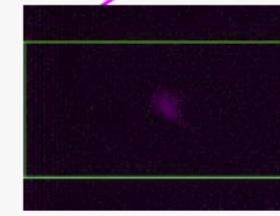
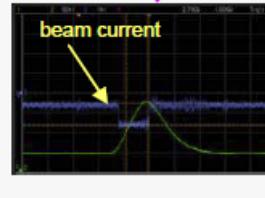
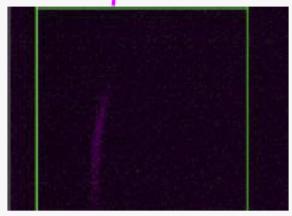
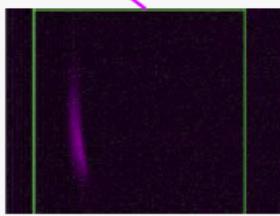
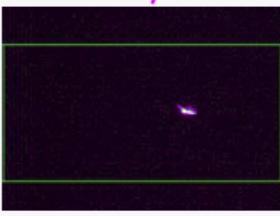


Injector



The 2nd arc

MS29



MS15

MS17

MS19

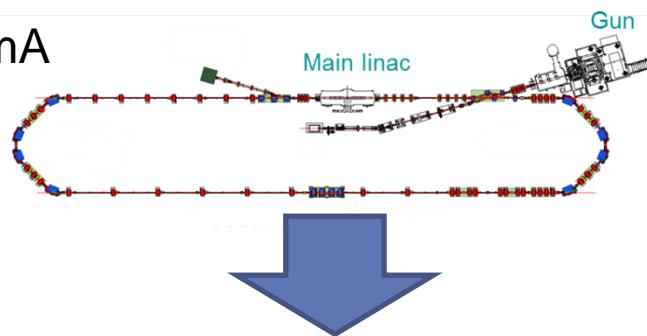
Movable FC

MS26

MS27

10-kW EUV for Lithography

35 MeV, 10 mA



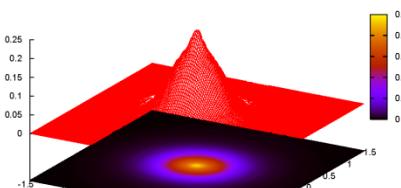
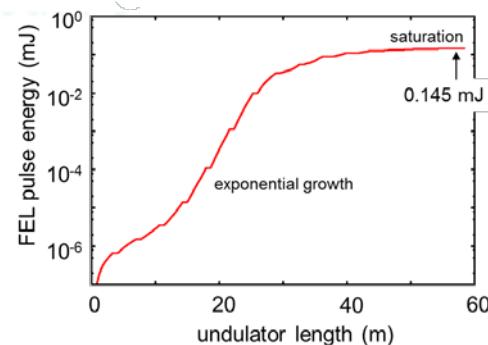
800 MeV, 8 mA

Main linac ~ 12.5 MV x 64 cavity

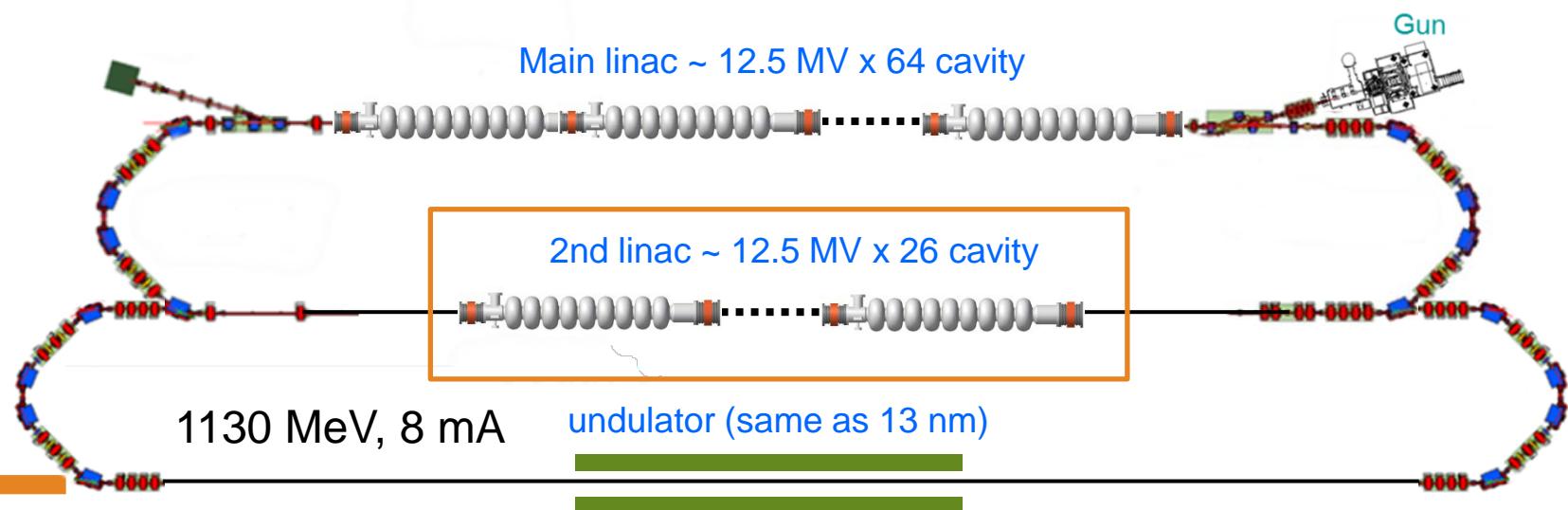
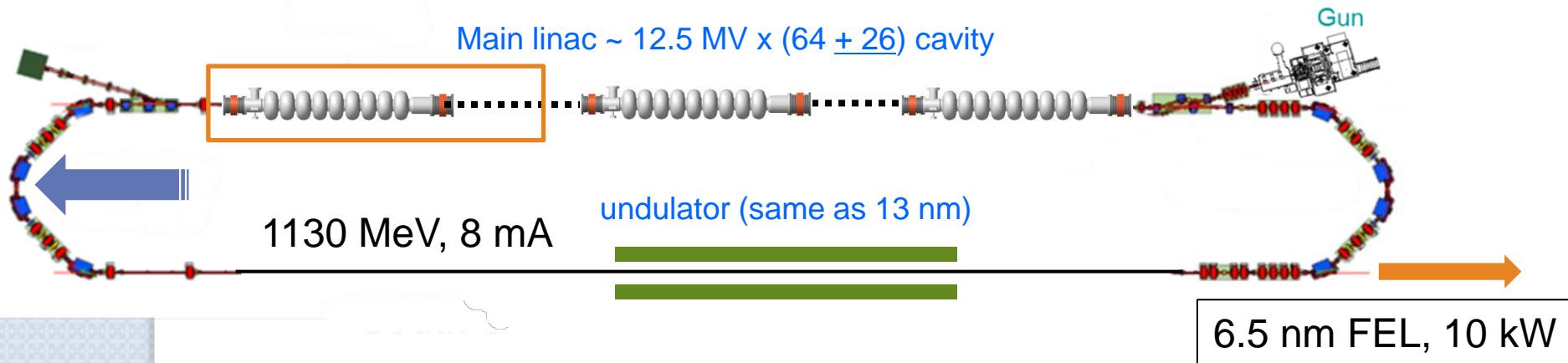
undulator

Gun

13 nm FEL, 10 kW



Possible Upgrade to 6.5 nm



6.5 nm FEL, 10 kW

Summary

- Design of 10-kW EUV-FELs
 - employ ERL similar to 14-kW IR-FEL
 - with up-to-date technology developed at KEK/JAEA
 - 800-MeV, 8-mA ERL produces 10-kW EUV
 - future upgrade to 6.5 nm
- Demonstration at cERL is ongoing
 - Electron gun and superconducting Acc.
 - small emittance beam
 - bunch compression
 - ...

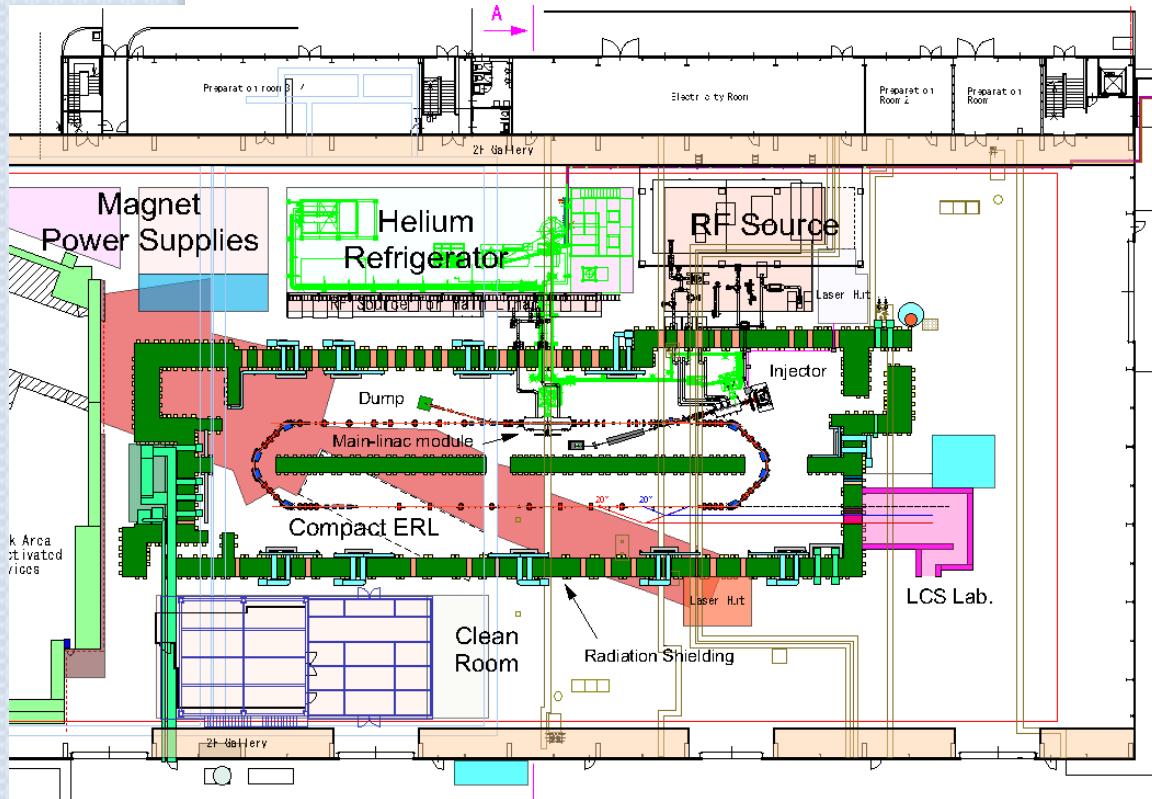
Thank you !



Compact ERL

Goals of the Compact ERL

- Demonstrate reliable operations of our R&D products (guns, SRF, ...)
- Demonstrate the generation and recirculation of ultra-low emittance beams



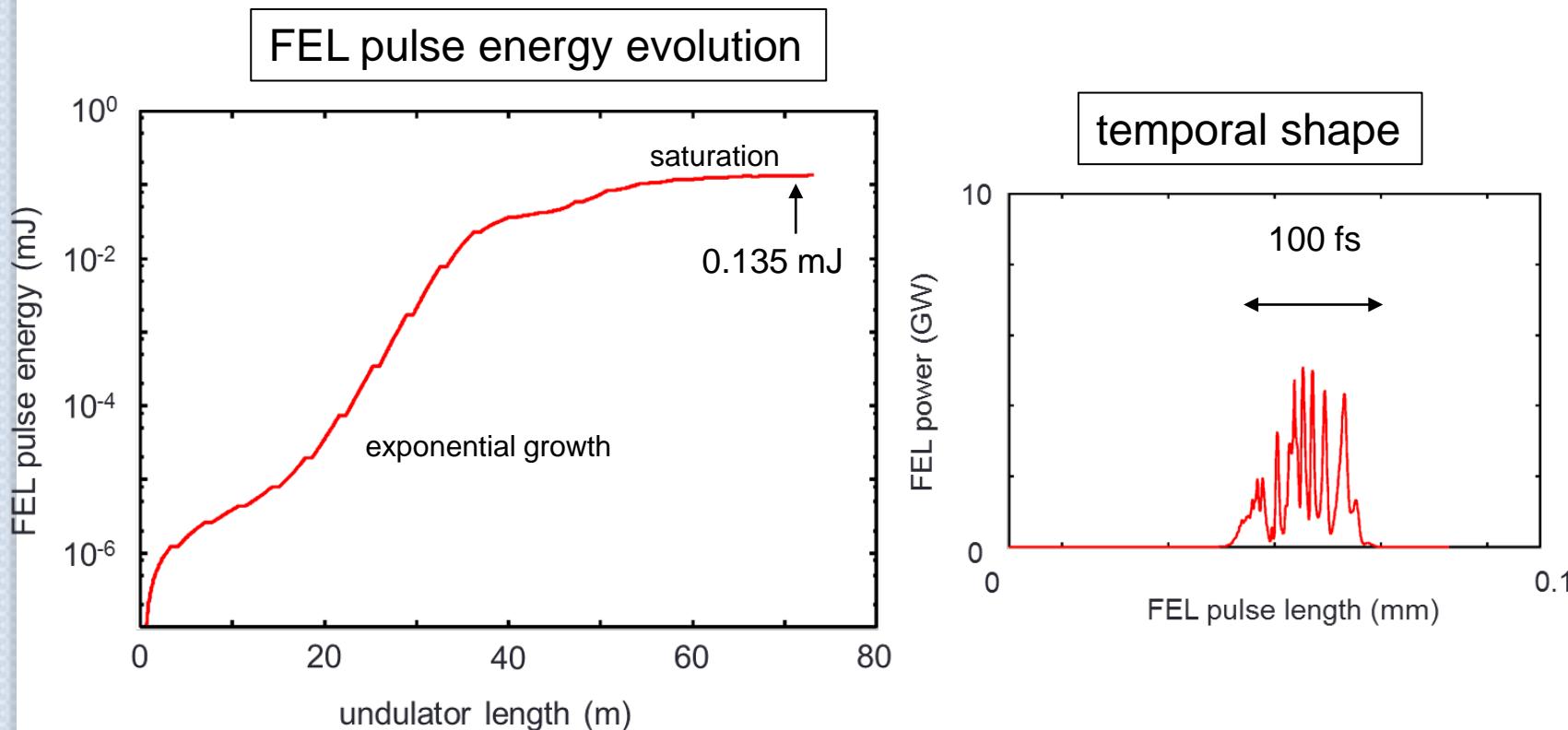
Parameters of the Compact ERL

| | Parameters |
|--------------------------------|---|
| Beam energy (upgradability) | 35 MeV 125 MeV (single loop) 245 MeV (double loops) |
| Injection energy | 5 MeV |
| Average current | 10 mA (100 mA in future) |
| Acc. gradient (main linac) | 15 MV/m |
| Normalized emittance | 0.1 mm·mrad (7.7 pC) 1 mm·mrad (77 pC) |
| Bunch length (rms) | 1 - 3 ps (usual) ~ 100 fs (with B.C.) |
| RF frequency | 1.3 GHz |

Simulation: FEL pulse evolution for 6.5nm

GENESIS simulations by N. Nishimori

$E=1130 \text{ MeV}$, $q=100 \text{ pC}$, $I_p=1000 \text{ A}$, $\varepsilon_n=0.8 \text{ mm-mrad}$,
rep.=81.25 MHz



$$0.135 \text{ mJ} \times 81.25 \text{ MHz} = 11 \text{ kW}$$